



SMBYW02-200

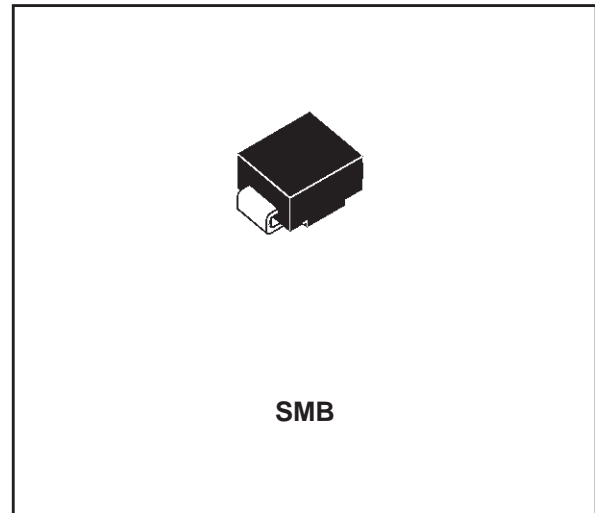
HIGH EFFICIENCY FAST RECOVERY RECTIFIER DIODES

FEATURES

- SUITED FOR SMPS
- VERY LOW FORWARD LOSSES
- NEGLIGIBLE SWITCHING LOSSES
- HIGH SURGE CURRENT CAPABILITY
- HIGH AVALANCHE ENERGY CAPABILITY
- SURFACE MOUNT DEVICE

DESCRIPTION

Single chip rectifier suited for Switch Mode Power Supply and high frequency DC to DC converters. Packaged in SMB, this surface mount device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$I_{F(RMS)}$	RMS forward current	10	A
$I_{F(AV)}$	Average forward current	2	A
I_{FSM}	Non repetitive surge peak forward current	50	A
T_{stg} T_j	Storage and junction temperature range	- 40 to + 150 - 40 to + 150	°C °C

Symbol	Parameter	Value	Unit
V_{RRM}	Repetitive peak reverse voltage	200	V

THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
$R_{th(j-l)}$	Junction-leads	25	°C/W

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ELECTRICAL CHARACTERISTICS STATIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
V_F *	$T_j = 25^\circ\text{C}$	$I_F = 6\text{ A}$			1.25	V
	$T_j = 100^\circ\text{C}$	$I_F = 2\text{ A}$		0.8	0.85	
I_R **	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			10	μA
	$T_j = 100^\circ\text{C}$			0.1	0.3	mA

Pulse test : * $t_p = 380\ \mu\text{s}$, duty cycle < 2 %

** $t_p = 5\ \text{ms}$, duty cycle < 2 %

RECOVERY CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
trr	$T_j = 25^\circ\text{C}$	$I_F = 1\text{ A}$ $V_R = 30\text{V}$ $dI_F/dt = -50\text{A}/\mu\text{s}$		26	35	ns
tfr	$T_j = 25^\circ\text{C}$	$I_F = 1\text{ A}$ $V_{FR} = 1.1 \times V_F$ $t_r = 10\ \text{ns}$		30		ns
V_{FP}	$T_j = 25^\circ\text{C}$	$I_F = 1\text{ A}$ $t_r = 10\ \text{ns}$		5		V

To evaluate the conduction losses use the following equation :

$$P = 0.7 \times I_{F(AV)} + 0.075 \times I_{F(RMS)}^2$$

Voltage (V)	200
Marking	A20

Laser marking
Logo indicates cathode

Fig.1 : Low frequency power losses versus average current.

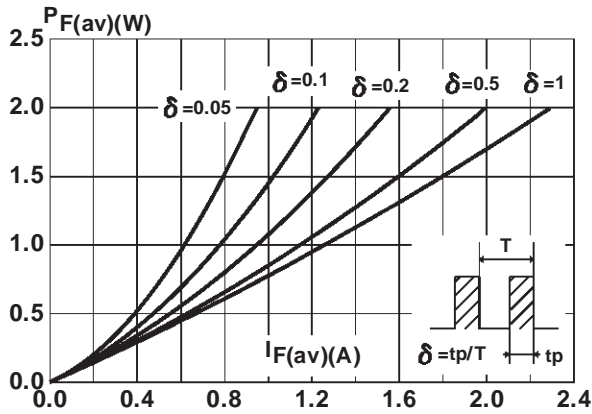


Fig.2 : Peak current versus form factor.

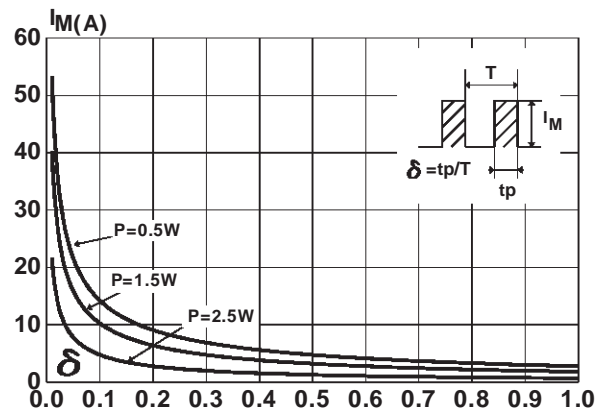


Fig.3 : Non repetitive surge peak forward current versus overload duration.

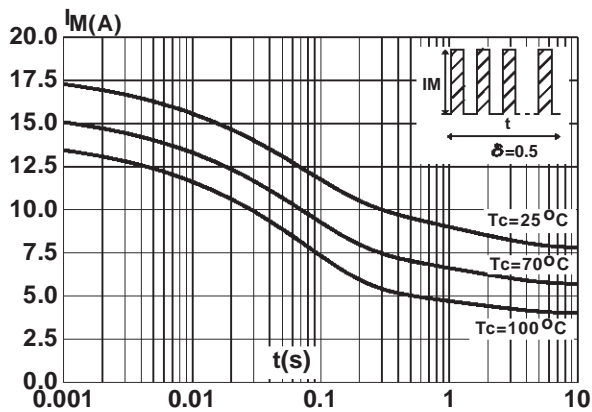


Fig.4 : Relative variation of thermal impedance junction to lead versus pulse duration.

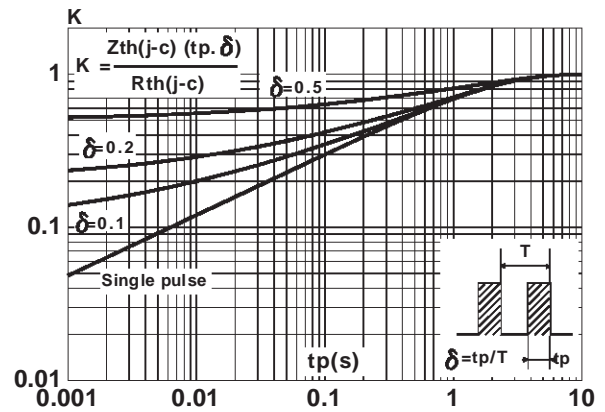


Fig.5 : Voltage drop versus forward current. (Maximum values)

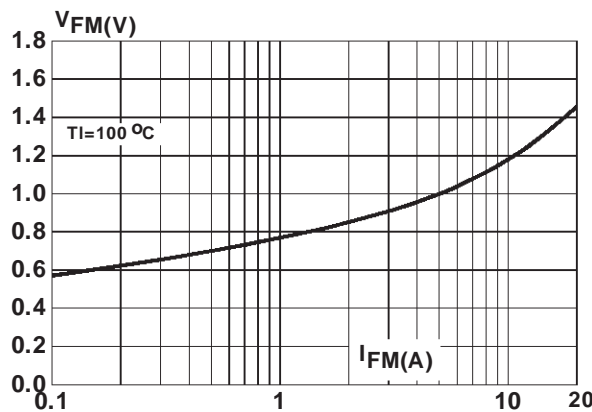
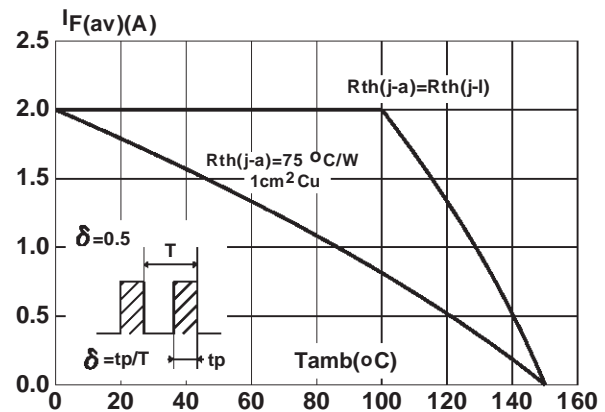


Fig.6 : Average current versus ambient temperature. (duty cycle : 0.5)



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Fig.7 : Capacitance versus reverse voltage applied.

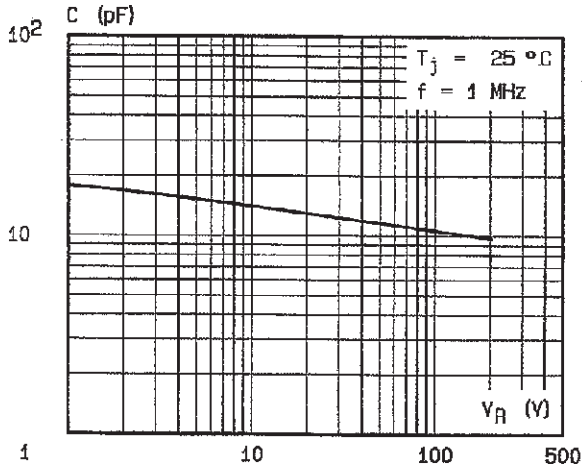


Fig.9 : Peak reverse current versus diF/dt.

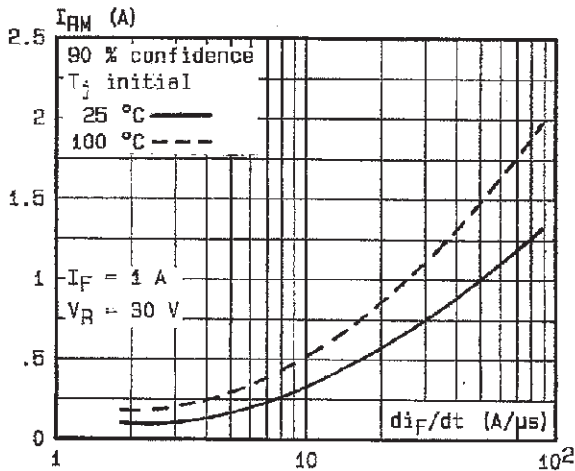


Fig.11 : Thermal resistance junction to ambient versus copper surface under each lead.

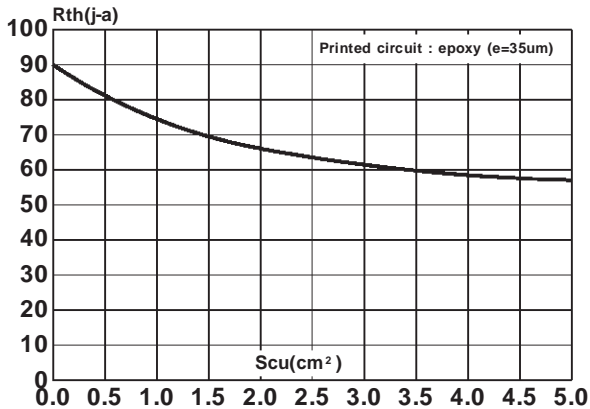


Fig.8 : Recovery time versus diF/dt.

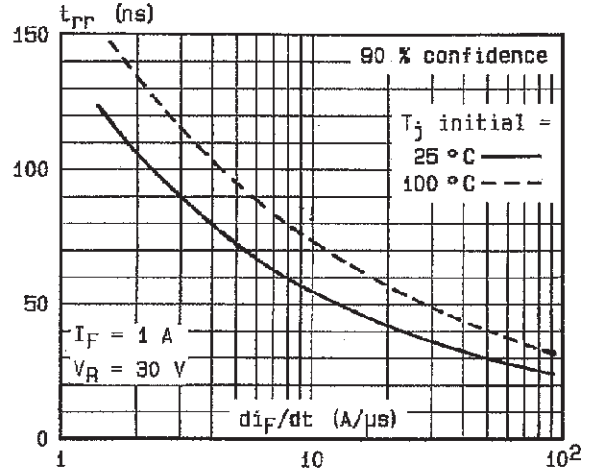
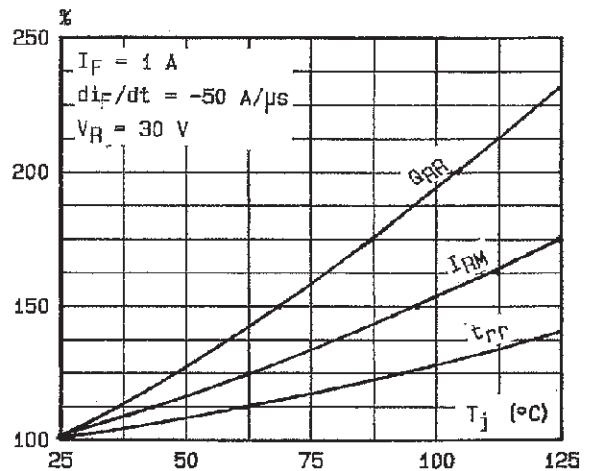
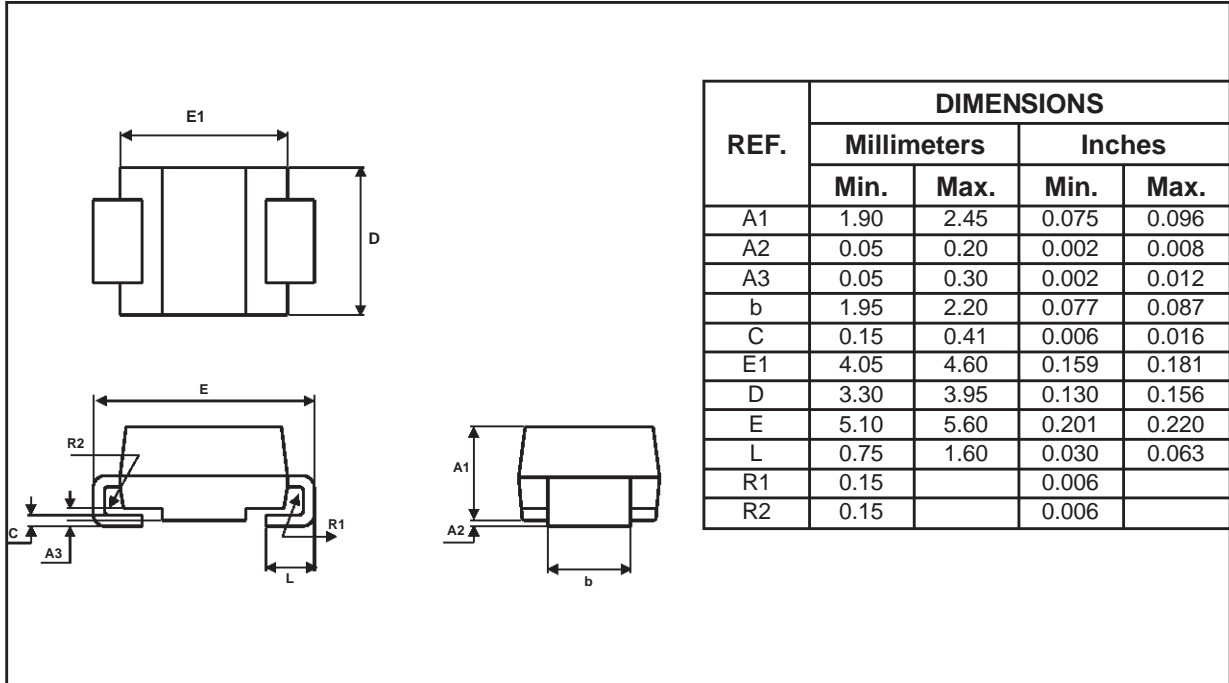


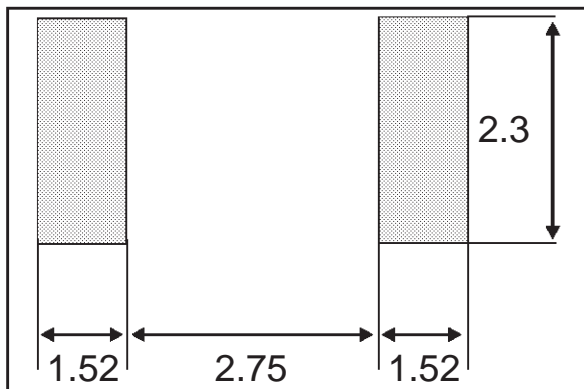
Fig.10 : Dynamic parameters versus junction temperature.



PACKAGE MECHANICAL DATA
SMB



FOOTPRINT DIMENSIONS (in millimeters)
SMB



- Weight : 0.12 g.
- Laser marking
- Logo indicates cathode

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